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	Application No.	Applicant(s)	• ~
Notice of Allowability	09/885,784	LIANG ET AL.	
	Examiner	Art Unit	
	Julio J. Maldonado	2823	
The MAILING DATE of this communication appear All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED) or other appropriate comn (IGHTS. This application is and MPEP 1308.	in this application. If not included nunication will be mailed in due c	d ourse. THIS
2. ☑ The allowed claim(s) is/are <u>2-8,12,13 and 16</u> .	10/00/2000.		
3. The drawings filed on 20 June 2001 are accepted by the E	Examiner.		
4. ☐ Acknowledgment is made of a claim for foreign priority una) ☐ All b) ☐ Some* c) ☐ None of the:) or (f).	
 Certified copies of the priority documents have 	e been received.		
2. Certified copies of the priority documents have	e been received in Applicat	ion No	
3. Copies of the certified copies of the priority documents have been received in this national stage application from the			
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received:			
5. Acknowledgment is made of a claim for domestic priority ureference was included in the first sentence of the specific	ation or in an Application D	ata Sheet. 37 CFR 1.78.	a specific
 (a) The translation of the foreign language provisional a 6. Acknowledgment is made of a claim for domestic priority u in the first sentence of the specification or in an Application 	nder 35 U.S.C. §§ 120 and	or 121 since a specific reference	was included
Applicant has THREE MONTHS FROM THE "MAILING DATE" o below. Failure to timely comply will result in ABANDONMENT of	f this communication to file this application. THIS TH	a reply complying with the requir REE-MONTH PERIOD IS NOT E	ements noted
7. A SUBSTITUTE OATH OR DECLARATION must be subminformal PATENT APPLICATION (PTO-152) which give	nitted. Note the attached EXes reason(s) why the oath	(AMINER'S AMENDMENT or NO or declaration is deficient.	TICE OF
8. CORRECTED DRAWINGS (as "replacement sheets") must (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No		ew (PTO-948) attached	
(b) ☐ including changes required by the proposed drawing correction filed, which has been approved by the Examiner.			
(c) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No			
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t	.84(c)) should be written on the margin according to 37 C	the drawings in the front (not the b FR 1.121(d).	ack) of
9. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT FOR T	SIT OF BIOLOGICAL MAT THE DEPOSIT OF BIOLOG	FERIAL must be submitted. No SICAL MATERIAL.	ote the
Attachment(s)			
1⊠ Notice of References Cited (PTO-892)	5∐ Notice of In	formal Patent Application (PTO-1	52)
 2 Notice of Draftperson's Patent Drawing Review (PTO-948) 3 Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No. 	6∐ Interview S	ummary (PTO-413), Paper No	·
	3), 7□ Examiner's	Amendment/Comment	
4 Examiner's Comment Regarding Requirement for Deposit of Biological Material	8⊠ Examiner's 9∏ Other	Statement of Reasons for Allowa	ince

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DETAILED ACTION

- 1. The final rejection as set forth in paper mailed on 07/08/2003 is withdrawn because the prior art of record, fail to disclose a dielectric isolated metallization pattern.
- 2. Claims 2-8, 12, 13 and 16 are pending in the application.

Allowable Subject Matter

- 3. Claim 2-8, 12, 13 and 16 are allowed.
- 4. The following is an examiner's statement of reasons for allowance:

The prior art of record, Kelly et al. to U.S. 6, 143,117 teach in Figs. 1-8 and related text a method to transfer thin film structures teach the steps of providing a first semiconductor substrate (40); forming over the first semiconductor substrate (40) at least one microelectronic device (44) to form from the first semiconductor substrate (40) a partially fabricated semiconductor integrated circuit microelectronic fabrication (44, 46); providing a second substrate (10); forming over the second substrate (10), in inverted order, metallization pattern (20, 26, 32, 34, 36, 38) intended to mate with the partially fabricated semiconductor integrated circuit microelectronic fabrication (44, 46); laminating the partially fabricated semiconductor integrated circuit microelectronic fabrication (44, 46) with the second substrate (10) to mate the partially fabricated semiconductor integrated circuit microelectronic fabrication (44, 46) with the metallization pattern (20, 26, 32, 34, 36, 38) to thus form a laminated completely fabricated semiconductor integrated circuit microelectronic fabrication (44, 46, 20, 26, 32, 34, 36, 38); and removing the second substrate (10) from the laminated completely

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fabricated semiconductor integrated circuit microelectronic fabrication (44, 46, 20, 26, 32, 34, 36, 38) while employing a dicing method (column 4, line 55 – column 9, line 43).

Kelly et al. fail to teach removing said second substrate while employing the dielectric isolated metallization pattern as an etch stop layer; and removing the second substrate from the laminated completely fabricated semiconductor integrated circuit microelectronic fabrication while employing a method selected from the group consisting of milling methods, polish methods and chemical mechanical polish (CMP) planarizing method; and teach away form using dielectric isolated metallization pattern.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

5. Papers related to this application may be submitted directly to Art Unit 2823 by facsimile transmission. Papers should be faxed to Art Unit 2823 via the Art Unit 2823 Fax Center located in Crystal Plaza 4, room 3C23. The faxing of such papers must conform to the notice published in the Official Gazette, 1096 OG 30 (15 November 1989). The Art Unit 2823 Fax Center number is (703) 305-3432. The Art Unit 2823 Fax Center is to be used only for papers related to Art Unit 2823 applications.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to **Julio J. Maldonado** at **(703) 306-0098** and between the hours of 8:00 AM to 4:00 PM (Eastern Standard Time) Monday through Friday or by e-

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mail via <u>julio.maldonado@uspto.gov</u>. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri, can be reached on (703) 306-2794.

Any inquiry of a general nature or relating to the status of this application should be directed to the **Group 2800 Receptionist** at **(703) 308-0956**.

JMR 1/6/04

George Fourson Primary Examiner